

General Description

The AGM14N10MNA combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

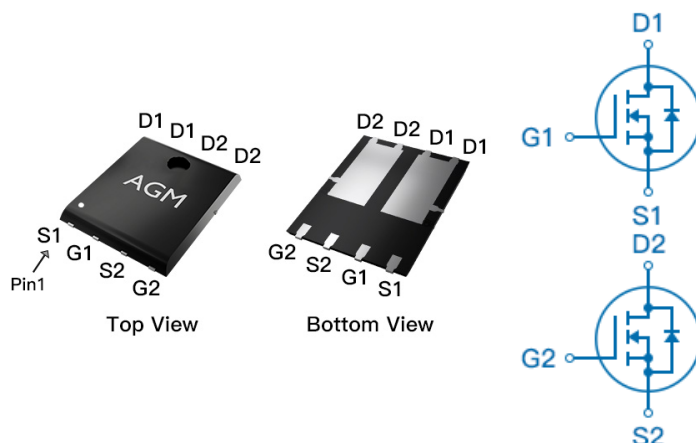
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
100V	13mΩ	50A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM14N10MNA	AGM14N10MNA	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	100	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	50	A
	Drain Current-Continuous(Tc=100°C)	35	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	200	A
PD	Maximum Power Dissipation(Tc=25°C)	70	w
	Maximum Power Dissipation(Tc=100°C)	28	w
EAS	Avalanche energy (Note 3)	64	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	20	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	1.78	°C/W

Table 3. N- Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Table 1: Channel Electrical Characteristics (V _{DS} =50V unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	--	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=8A	--	8.0	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=10A	--	13	16	mΩ
		VGS=4.5V, ID=8A	--	16	20	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=40V,VGS=0V, F=1MHZ	--	930	--	pF
Coss	Output Capacitance		--	315	--	pF
Crss	Reverse Transfer Capacitance		--	2.5	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	6.0	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=50V, ID=10A,REGEN=1.6Ω	--	6.0	--	nS
tr	Turn-on Rise Time		--	2.0	--	nS
td(off)	Turn-Off Delay Time		--	18	--	nS
tf	Turn-Off Fall Time		--	2.0	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V,ID=10A	--	16.5	--	nC
Qgs	Gate-Source Charge		--	3.0	--	nC
Qgd	Gate-Drain Charge		--	3.1	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	50	A
VSD	Forward on Voltage	VGS=0V,IS=10A	--	--	1.2	V
trr	Reverse Recovery Time	IF=10A , dI/dt=100A/μs , TJ=25℃	--	40	--	ns
Qrr	Reverse Recovery Charge		--	52	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 3.EAS condition: T_J=25°C

Characteristics Curve:

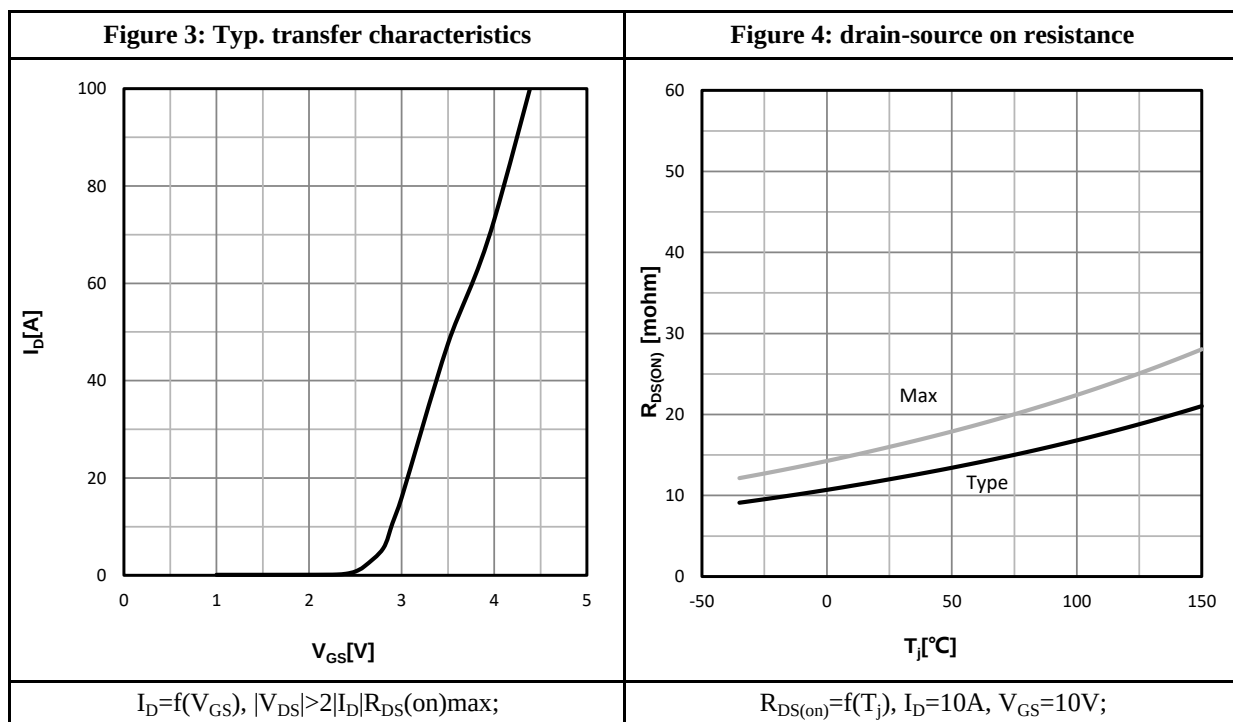
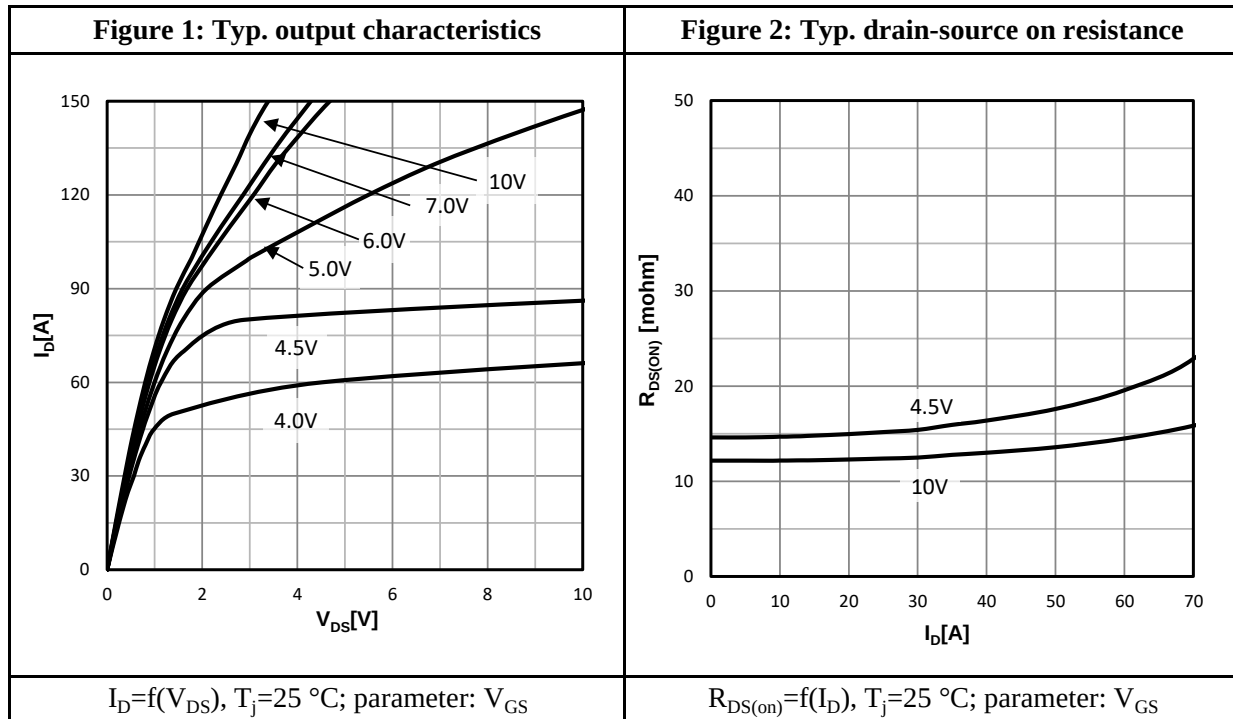
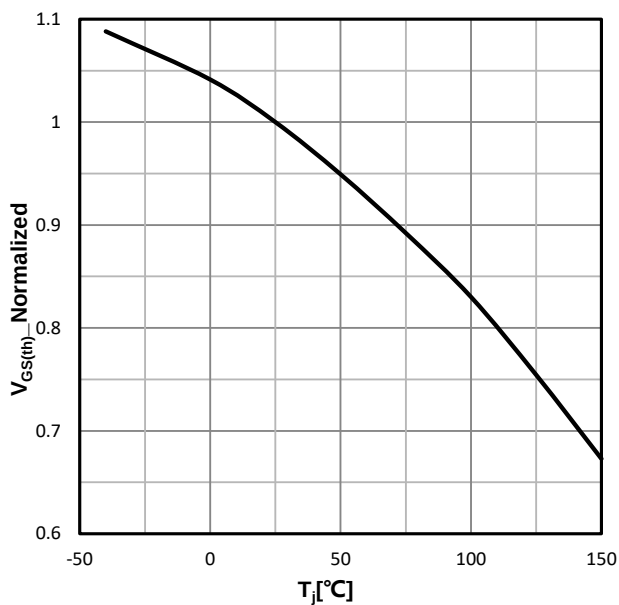
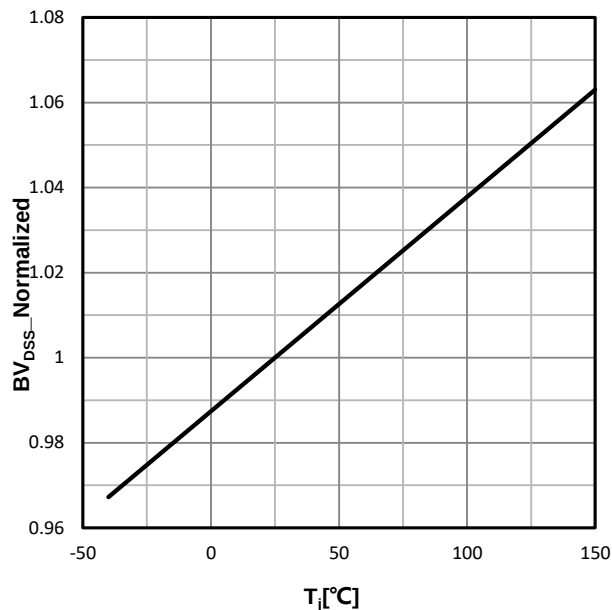


Figure 5: Typ. gate threshold voltage



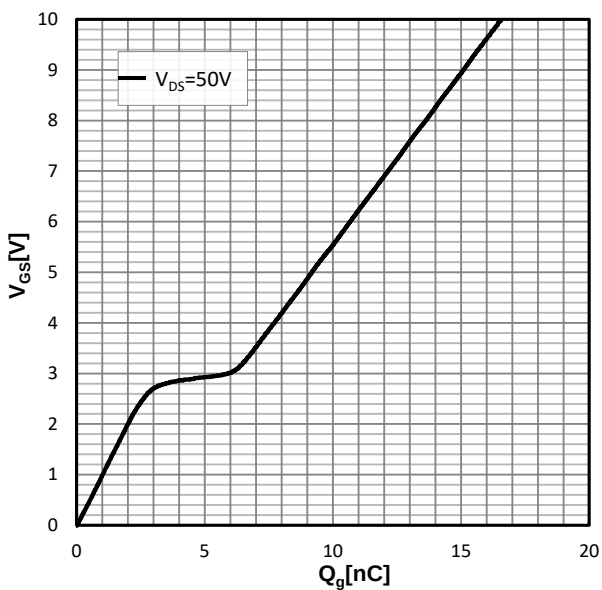
$$V_{GS}=f(T_j), I_{V_{GS}}=V_{DS}, I_D=250\mu A;$$

Figure 6: Drain-source breakdown voltage



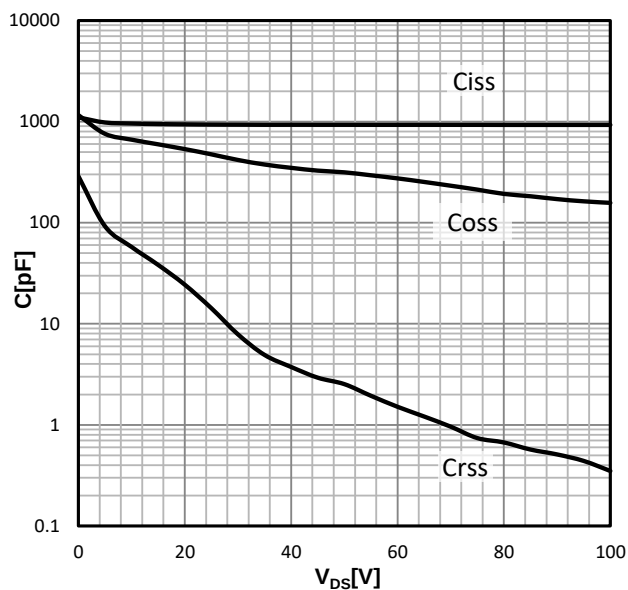
$$V_{BR(DSS)}=f(T_j); I_D=250\mu A;$$

Figure 7: Typ. gate charge



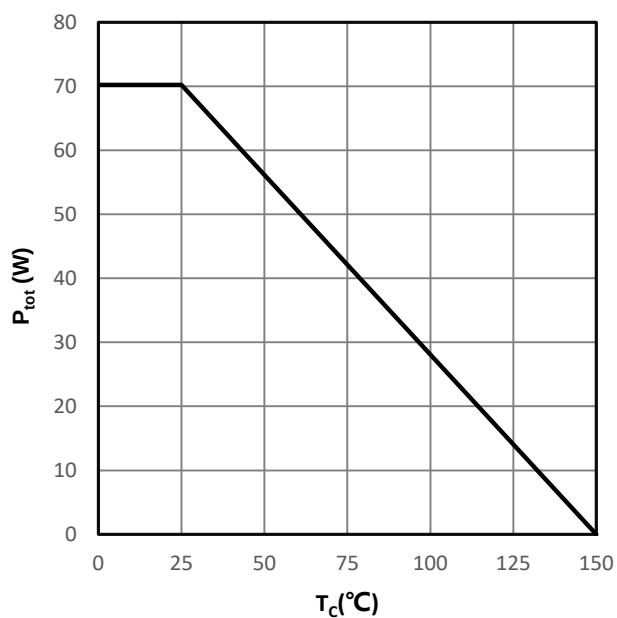
$$V_{GS}=f(Q_g), I_D=10A, T_j=25\text{ }^{\circ}\text{C}; \text{ parameter: } V_{DS}$$

Figure 8: Typ. Capacitances



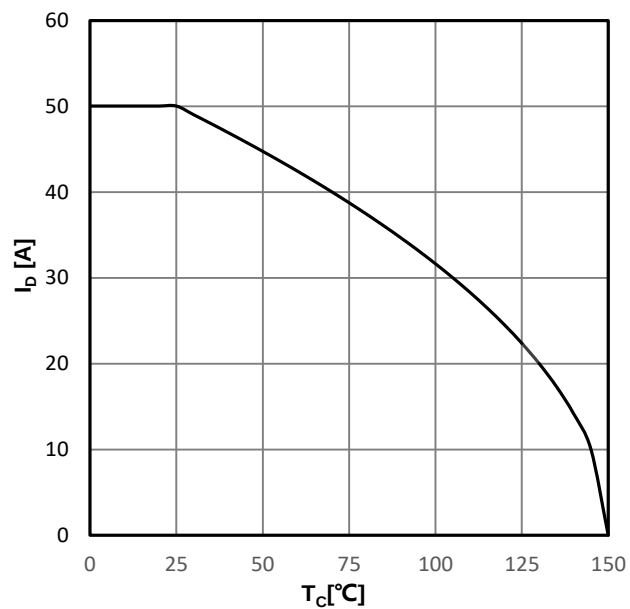
$$C=f(V_{DS}); V_{GS}=0V; f=1.0\text{ MHz};$$

Figure 9: Power dissipation



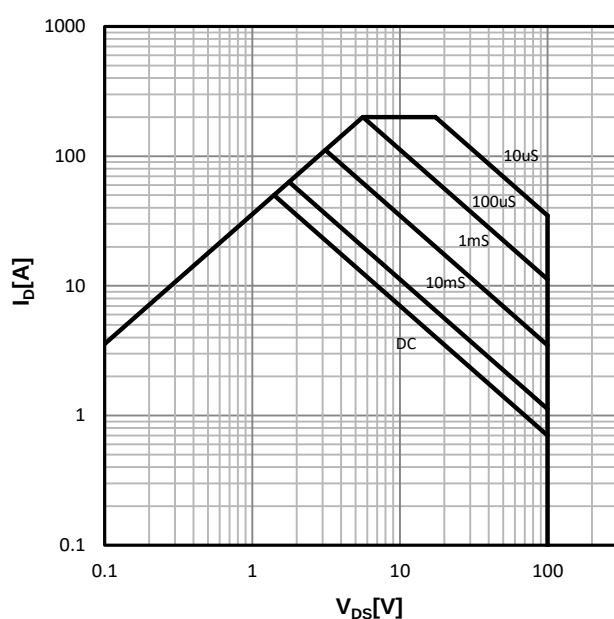
$$P_{tot}=f(T_C);$$

Figure 10: Drain current



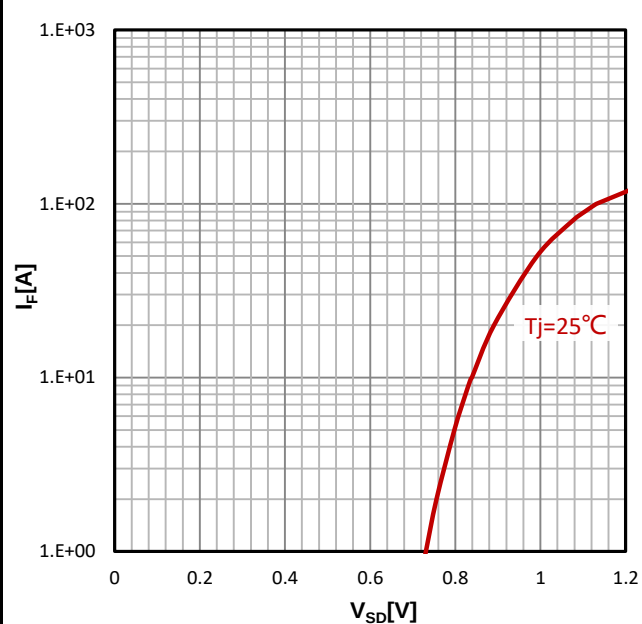
$$I_D=f(T_C);$$

Figure 11: Safe operating area



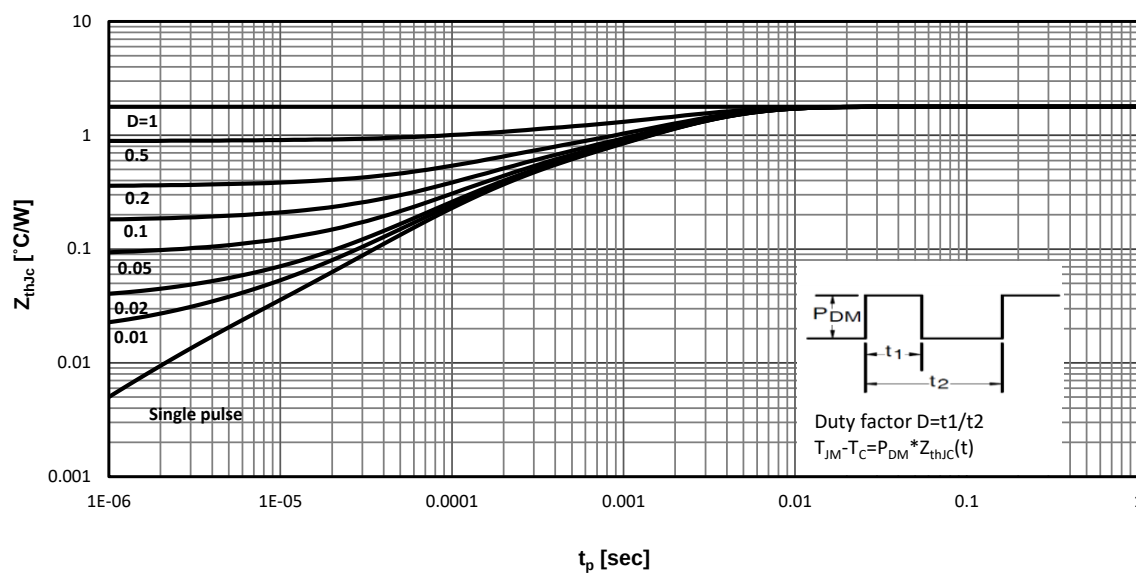
$$I_D=f(V_{DS}); T_C=25\text{ }^{\circ}\text{C}; D=0; \text{parameter: tp}$$

Figure 12: Typ. forward characteristics



$$I_F=f(V_{SD});$$

Figure 13: Max. Transient Thermal Impedance



$$Z_{thJC}=f(t_p); \text{ parameter: } D$$

Test Circuit & Waveform:

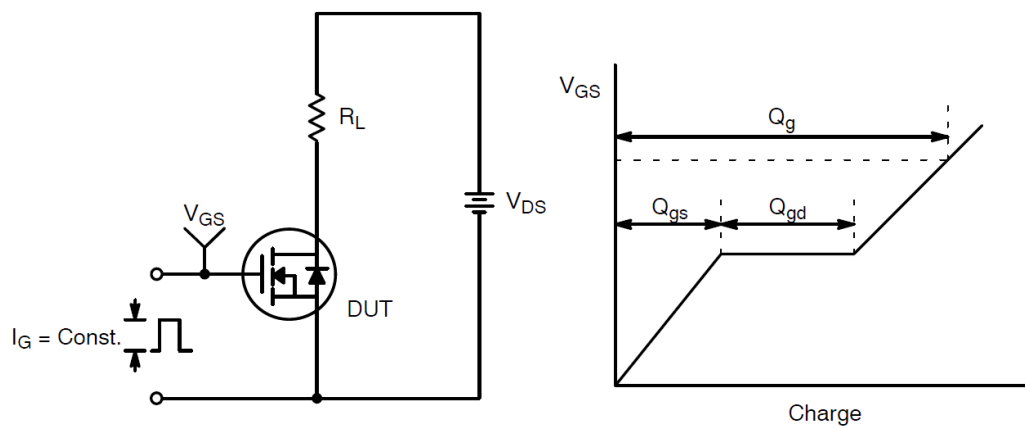


Figure 14: Gate Charge Test Circuit & Waveform

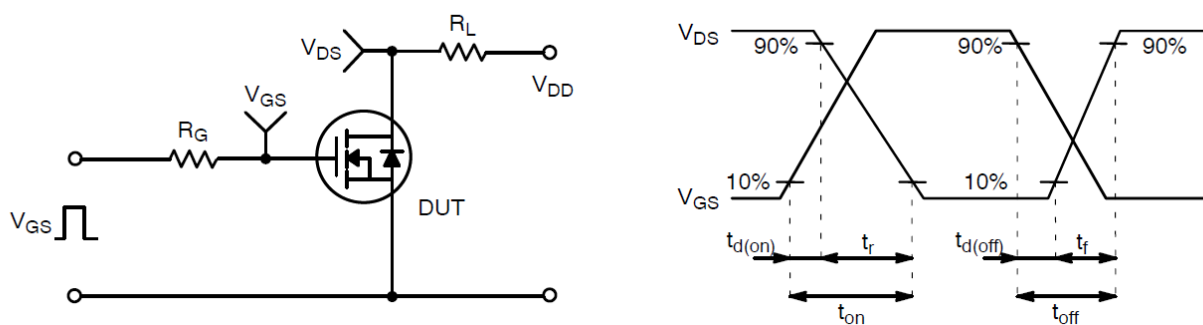


Figure 15: Resistive Switching Test Circuit & Waveforms

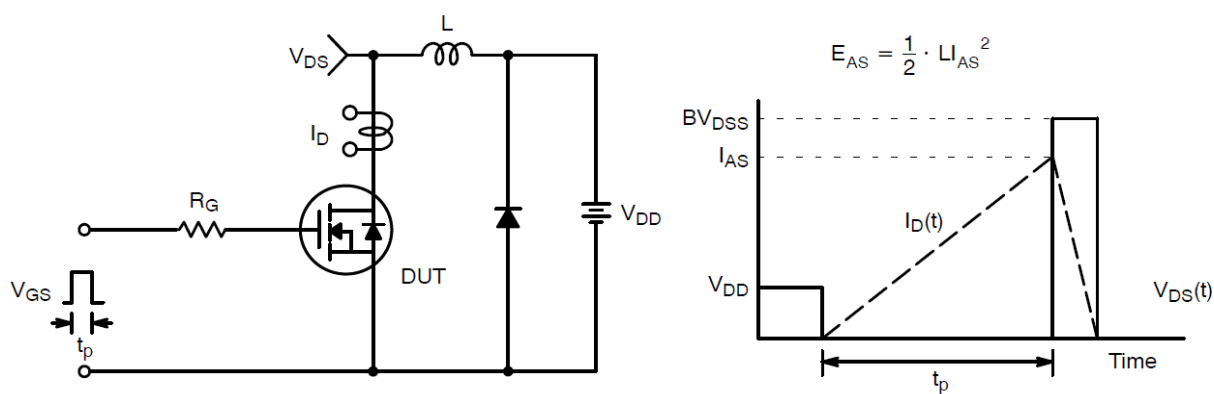
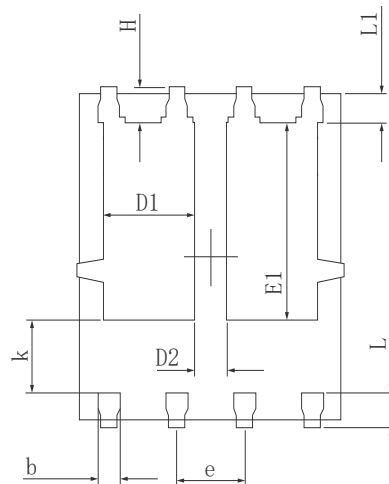
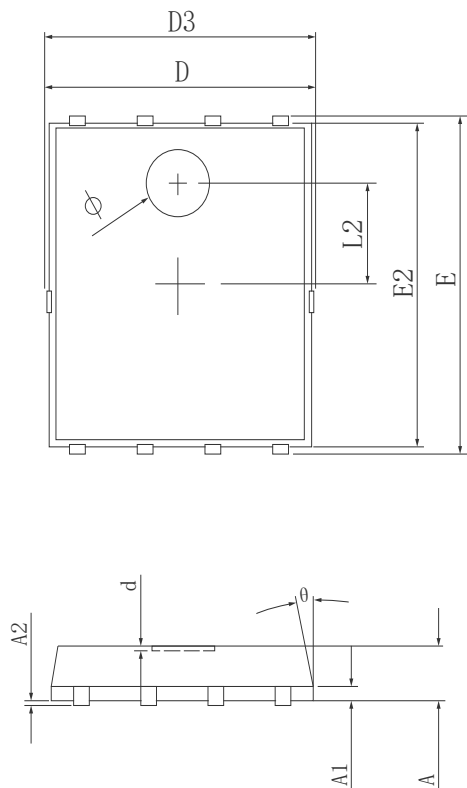
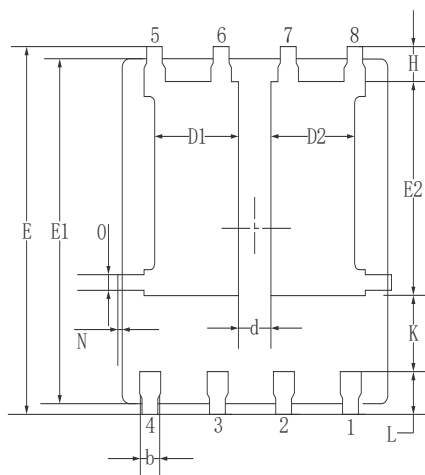
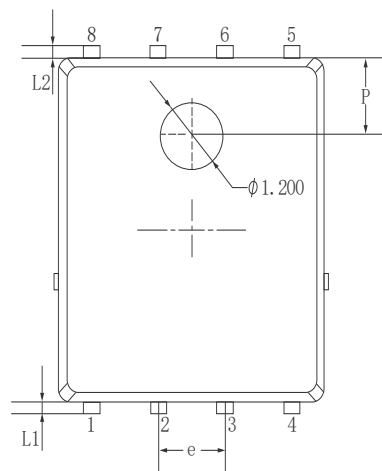


Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

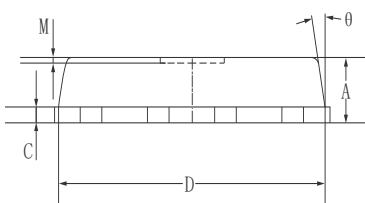
Dimensions (PDFN5*6)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0°0.05		
D	4.824	4.900	4.976
D1	1.605	1.705	1.805
D2	0.500	0.600	0.700
D3	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100



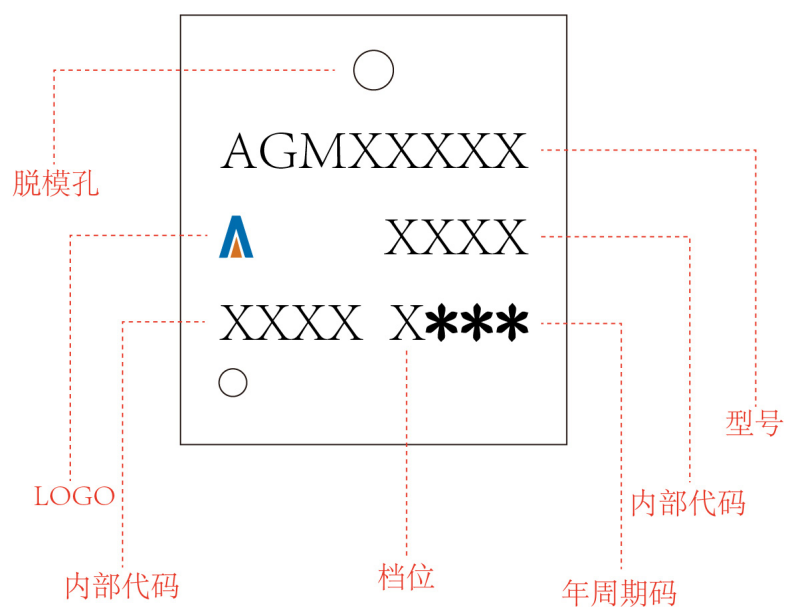
Symbol	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1/D2	1.51	1.61	1.71
d	0.50	0.60	0.70
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		



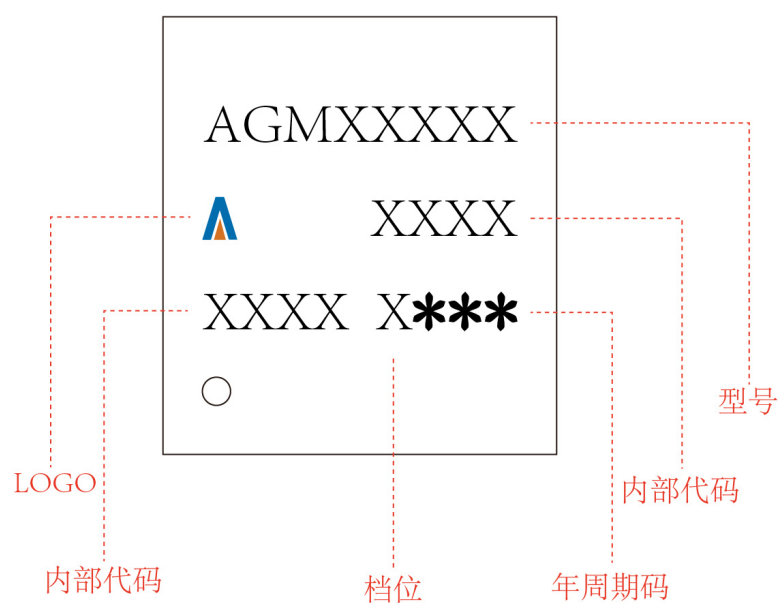
PDFN5*6

Marking Instructions:

Model1:



Model2:



Disclaimer:

The information provided in this document is believed to be accurate and reliable. However, Shenzhen Core Control Source Electronics Technology Co., Ltd. does not assume any responsibility for the following consequences. Do not consider the use of such information or use beyond its scope.

The information mentioned in this document may be changed at any time without notice.

The products and information provided in this document do not infringe patents. Shenzhen Core Control Source Electronics Technology Co., Ltd. assumes no responsibility for any infringement of any other rights of third parties. The result of using such products and information.

This document is the third version issued on Sep.15th, 2024. This document replaces all previously provided information.

 It is a registered trademark of Shenzhen Core Control Source Electronics Technology Co., Ltd.

Copyright © 2017 Shenzhen Core Control Source Electronics Technology Co., Ltd. all rights reserved.